

In the Specification:

Please rewrite the title to:

A Nonvolatile Memory Cell, Memory Cell Arrangement And Method
Method For Production Of A Nonvolatile Memory Cell

Please insert before the first paragraph of the application:

PRIORITY CLAIM

This application is the national stage application of international application number PCT/DE03/03588, filed on October 29, 2003, which claims the benefit of priority to German Patent Application 102 50 829.1, filed on October 31, 2002, herein incorporated by reference.

Please insert before the paragraph beginning on page 1, line 7 of the application:

TECHNICAL FIELD

Please insert before the paragraph beginning on page 1, line 11 of the application:

BACKGROUND

Please insert before the paragraph beginning on page 3, line 25 of the application:

BRIEF SUMMARY

Please delete the paragraph on page 3, lines 30-33.

Please insert before the paragraph beginning on page 12, line 31 of the application:

BRIEF DESCRIPTION OF THE DRAWINGS

Please insert before the paragraph beginning on page 13, line 28 of the application:

DETAILED DESCRIPTION

Please rewrite the paragraph on page 14, lines 14-24 as follows:

To obtain the layer sequence 100-110 shown in Fig. 1B, a second electrically insulating layer 111 is deposited on the layer sequence 100 and planarized using a CMP (chemical mechanical polishing) process, with the gate region 104 as stop layer. Furthermore, using a lithography process and an etching process, via holes 112 are introduced into the gate region 104 and into the first electrically insulating layer 103. This obviously forms a porous mask, with the pores or via holes 112 being used as templates for the growth of carbon nanotubes in a subsequent method step.

Please rewrite the paragraph on page 16, lines 27-30 as follows:

The following text, referring to Fig. 2A to Fig. 2A2F, describes a method for fabricating a memory cell in accordance with a second exemplary embodiment of the invention.